

**REMARKS**

At the outset, the Examiner is thanked for the thorough review and consideration of the pending application. The Office Action dated November 16, 2005 has been received and its contents carefully reviewed.

Claim 1 is hereby amended. No new matter is added. Claims 1-21 are currently pending. Claims 1-10 are examined and claims 11-21 are withdrawn from consideration. Reexamination and reconsideration of the examined claims is respectfully requested.

In the Office Action, claim 1 is objected to as being indefinite for failing to particularly point out and distinctly claim the subject matter which applicant regards as the invention. Applicant hereby amends claim 1 to overcome the objection. Accordingly, Applicant respectfully requests the withdrawal of the objection to claim 1.

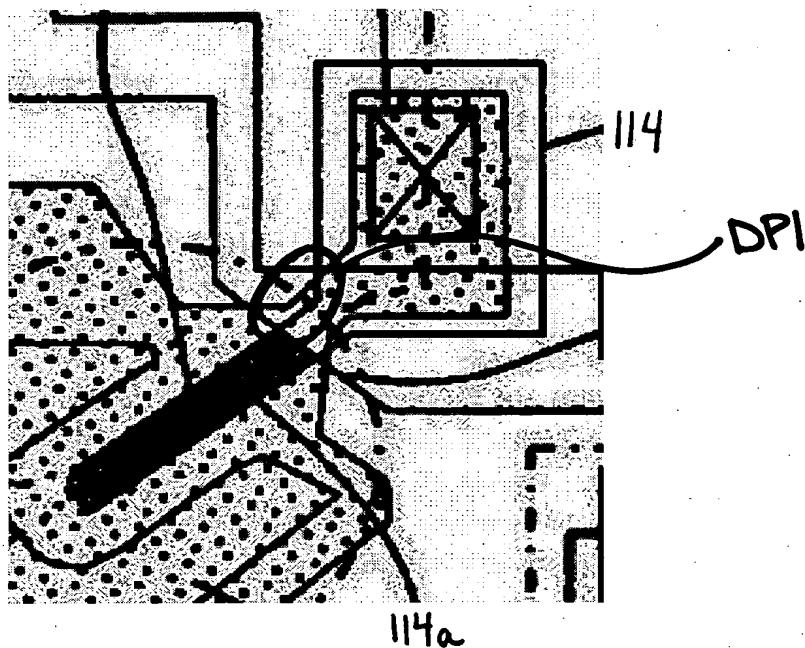
Also, in the Office Action, claims 1-6 and 9-10 are rejected under 35 U.S.C. § 102(e) as being anticipated by U.S. Patent No. 6,671,010 to Kwon et al. (hereinafter “Kwon”). Claims 7 and 8 are objected to as being dependent upon a rejected base claim, but would be allowable if rewritten in independent form. Applicant appreciates the Examiner’s indication that claims 7 and 8 recite allowable subject matter.

Applicant respectfully traverses the rejection of claims 1-6 and 9-10 as being anticipated by Kwon.

Claim 1 is allowable over Kwon in that claim 1 recites a combination of elements including for example, “a semiconductor layer having an active layer over the gate electrode, a first extended portion, and a neck region connecting the active layer and the first extended portion, wherein the first extended portion and the neck region correspond to the drain electrode, and wherein both sides of the neck region are completely covered with the drain electrode parallel to an extended direction of the drain electrode toward the source electrode.” Kwon does not teach at least these features of the claimed invention. Specifically, the structure of claim 1 is different from the structure of Kwon in that “both sides of the neck region are completely covered with the drain electrode parallel to an extended direction of the drain electrode toward

the source electrode.” However, Kwon teaches the neck region is only partially covered by the drain electrode. On page 6 of the Office Action, the Examiner alleges that Kwon teaches the neck region is completely covered with the drain electrode and points to the dotted circle area of Fig. 6I of Kwon. However, a magnified portion of Fig. 6I of Kwon is reproduced below:

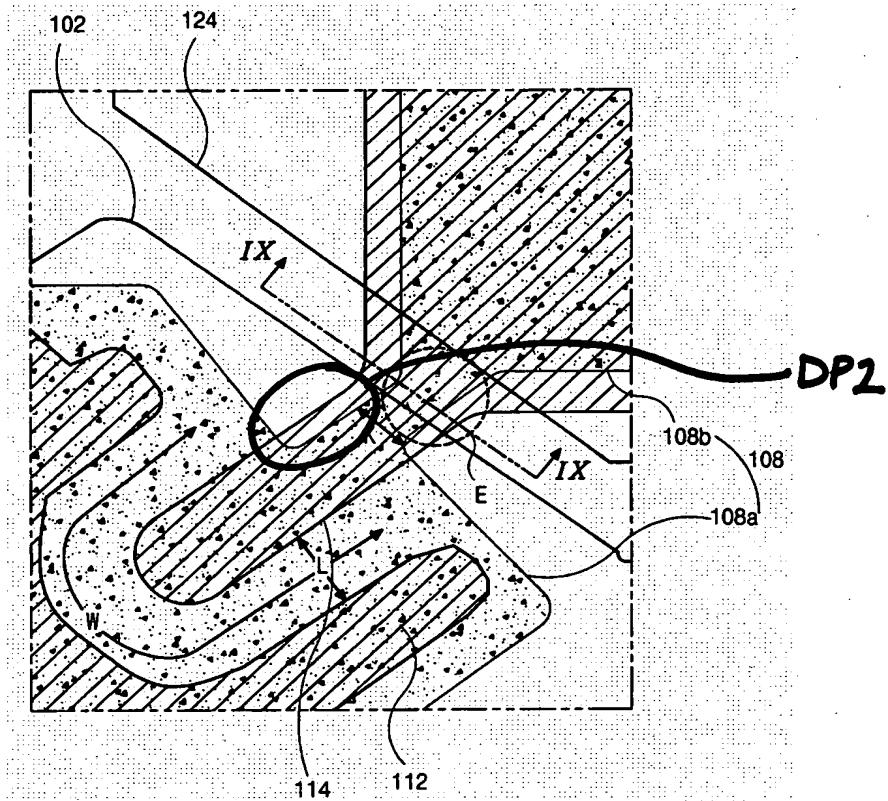
Kwon (FIG. 6I)



The dotted area represents the active layer 116. The drain electrode 114 and drain protrusion 114a are also shown. See column 8, lines 12-29. As shown, a line of the active layer 116 in “DP1” is disposed outside of the drain electrode 114. Thus, Kwon does not teach “both sides of the neck region are completely covered with the drain electrode.”

As shown in Fig. 7 of the present invention, the neck region of semiconductor layer 108 is “completely covered by with the drain electrode” 114. Fig. 7 of the present invention is reproduced below.

The present invention (FIG. 7)



As shown, a line of the neck region of the semiconductor layer 108 in DP2 is disposed inside the drain electrode 114 and is completely covered by the drain electrode 114.

Thus, Kwon does not teach “a semiconductor layer having an active layer over the gate electrode, a first extended portion, and a neck region connecting the active layer and the first extended portion, wherein the first extended portion and the neck region correspond to the drain electrode, and wherein both sides of the neck region are completely covered with the drain electrode parallel to an extended direction of the drain electrode toward the source electrode.” Accordingly, because Kwon fails to teach these features of claim 1, Applicant respectfully submits that claim 1 and claims 2-6 and 9-10, which depend therefrom, are allowable over Kwon.

Applicant believes the foregoing amendments place the application in condition for allowance and early, favorable action is respectfully solicited.

If for any reason the Examiner finds the application other than in condition for allowance, the Examiner is requested to call the undersigned attorney at (202) 496-7500 to discuss the steps necessary for placing the application in condition for allowance. All correspondence should continue to be sent to the below-listed address.

If these papers are not considered timely filed by the Patent and Trademark Office, then a petition is hereby made under 37 C.F.R. § 1.136, and any additional fees required under 37 C.F.R. § 1.136 for any necessary extension of time, or any other fees required to complete the filing of this response, may be charged to Deposit Account No. 50-0911. Please credit any overpayment to deposit Account No. 50-0911. A duplicate copy of this sheet is enclosed.

Dated: February 16, 2006

Respectfully submitted,

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